



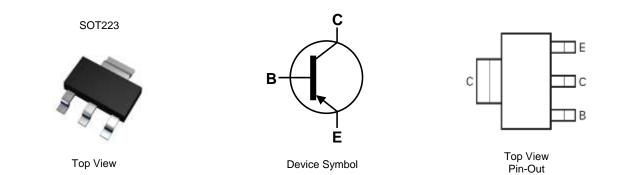
20V PNP MEDIUM POWER TRANSISTOR IN SOT223

Features

- BV_{CEO} > -20V
- I_C = -6A High Continuous Collector Current
- I_{CM} = -20A Peak Pulse Current
- Low Saturation Voltage V_{CE(SAT)}
- h_{FE} Specified up to -20A for a High Gain Hold-up
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: SOT223
- Case Material: Molded Plastic. "Green" Molding Compound. UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads. Solderable per MIL-STD-202, Method 208 3
- Weight: 0.112 grams (Approximate)



Ordering Information (Note 4)

Product	Compliance	Marking	Reel Size (inches)	Tape Width (mm)	Quantity per Reel
FZT948TA	AEC-Q101	FZT948	7	12	1,000

1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.

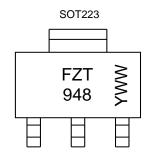
2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green"

and Lead-free. 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information

Notes:



FZT 948 = Product Type Marking Code YWW = Date Code Marking Y or \overline{Y} = Last Digit of Year (ex: 7 = 2017) WW or $\overline{W}W$ = Week Code (01 to 53)



Absolute Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{сво}	-40	V
Collector-Emitter Voltage	V _{CEO}	-20	V
Emitter-Base Voltage	V _{EBO}	-7	V
Continuous Collector Current	Ι _C	-6	А
Peak Pulse Current	I _{CM}	-20	А

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Power Dissipation	(Note 5)	5	3.0 24	W	
Linear Derating Factor	(Note 6)		1.6 12.8	mW /°C	
Thermal Desistance Junction to Ambient	(Note 5)	R _{θJA}	42		
Thermal Resistance, Junction to Ambient	(Note 6)	R _{θJA}	78	°C/W	
Thermal Resistance Junction to Lead	(Note 7)	R _{θJL}	8.84	1	
Operating and Storage Temperature Range	·	TJ, TSTG	-55 to +150	°C	

ESD Ratings (Note 8)

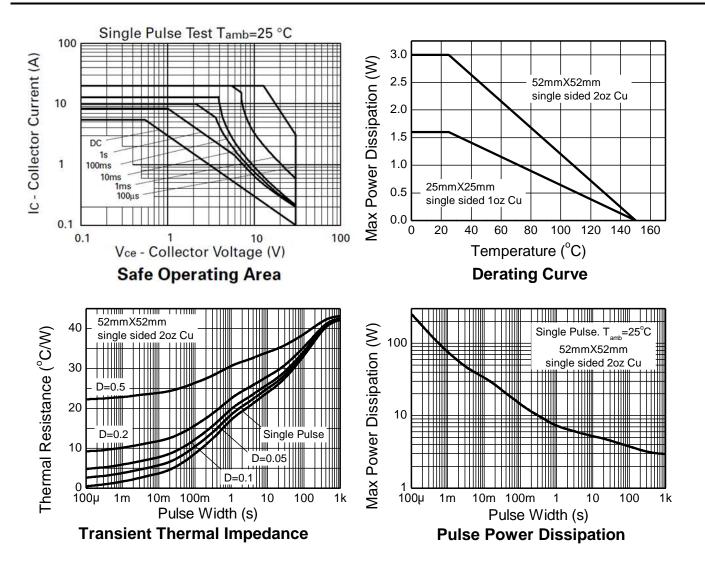
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3B
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

Notes: 5. For a device mounted with the collector lead on 52mm x 52mm 2oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in steady-state.

Same as Note 5, except the device is mounted on 25mm x 25mm 1oz copper.
Thermal resistance from junction to solder-point (at the end of the collector lead).
Refer to JEDEC specification JESD22-A114 and JESD22-A115.



Thermal Characteristics and Derating Information





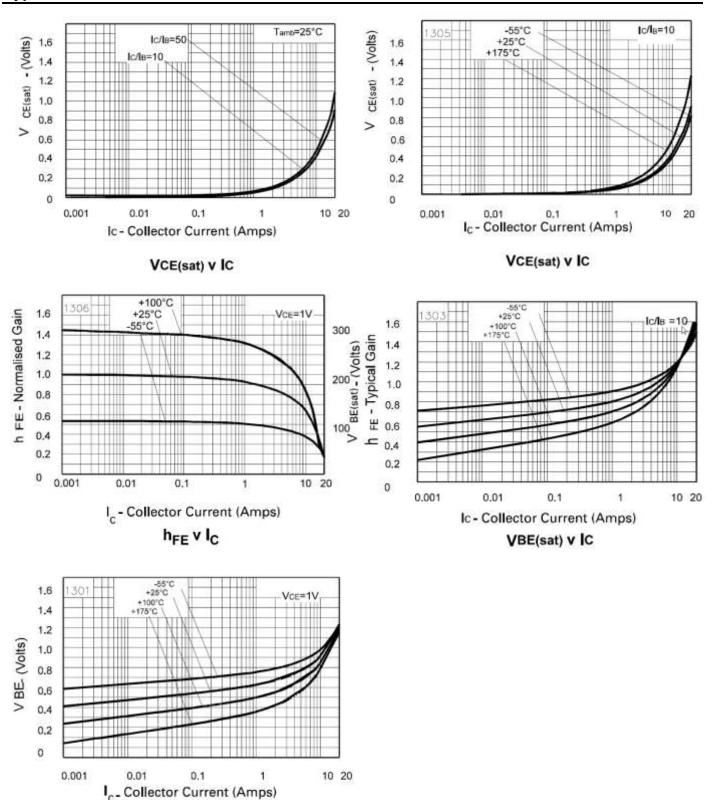
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
	Symbol		Тур	wax		
Collector-Base Breakdown Voltage	BV _{CBO}	-40	-55	—	V	$I_{\rm C} = -100\mu A$
Collector-Emitter Breakdown Voltage (Note 9)	BV _{CER}	-40	-55		V	$I_{C} = -1\mu A, R_{B} \le 1k\Omega$
Collector-Emitter Breakdown Voltage (Note 9)	BV _{CEO}	-20	-30	—	V	I _C = -10mA
Emitter-Base Breakdown Voltage	BV _{EBO}	-7	-8		V	I _E = -100μA
Collector Cut-Off Current		_	_	-50	nA	$V_{CB} = -30V$
	ICBO			-1	μA	V _{CB} = -30V, T _A = +100°C
Collector Cut-Off Current	I _{CER}	_		-50	nA	$V_{CE} = -30V, R \le 1k\Omega$
Collector Gut-On Current	OLIN		—	-1	μΑ	V _{CE} = -30V, T _A = +100°C
Emitter Cut-Off Current	I _{EBO}	_	_	-10	nA	V _{EB} = -6V
		100	200	_	_	$I_{C} = -10 \text{mA}, V_{CE} = -1 \text{V}$
		100	200	300		$I_{C} = -1A, V_{CE} = -1V$
DC Current Transfer Static Ratio (Note 9)	hFE	75	160	_		I _C = -5A, V _{CE} = -1V
		60	130	_		I _C = -10A, V _{CE} = -1V
		15	40	_		$I_{C} = -20A, V_{CE} = -2V$
		_	-60	-130	mV	$I_{C} = -0.5A, I_{B} = -10mA$
Collector-Emitter Saturation Voltage (Note 9)	M	—	-110	-180		$I_{\rm C} = -2A, I_{\rm B} = -200 {\rm mA}$
Collector-Emiller Saturation Voltage (Note 9)	V _{CE(SAT)}	_	-200	-280		$I_{C} = -4A, I_{B} = -400mA$
		—	-360	-450		$I_{C} = -6A, I_{B} = -250mA$
Base-Emitter Saturation Voltage (Note 9)	V _{BE(SAT)}	_	-1,050	-1,200	mV	I _C = -5A, I _B = -300mA
Base-Emitter Turn-On Voltage (Note 9)	V _{BE(ON)}	_	-870	-1,050	mV	I _C = -6A, V _{CE} = -1V
Transitional Frequency (Note 9)	f _T	_	80	_	MHz	I _C = -100mA, V _{CE} = -10V, f = 50MHz
Output Capacitance	C _{OBO}		163		pF	V _{CB} = -10V, f = 1MHz
Quitabia a Tirra	ton		120	_		$V_{CC} = -10V, I_{C} = -4A,$
Switching Time	toff	_	126	_	ns	$-I_{B1} = I_{B2} = -400 \text{mA}$

Note: 9. Measured under pulsed conditions. Pulse width \leq 300µs. Duty cycle \leq 2%.



Typical Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

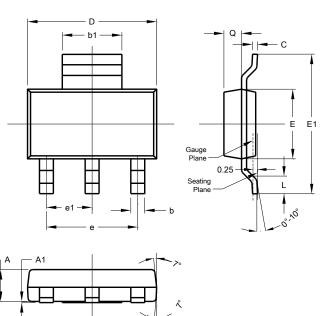


VBE(on) VIC



Package Outline Dimensions

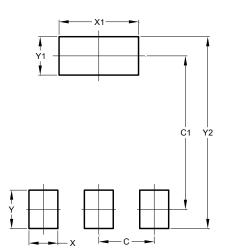
Please see http://www.diodes.com/package-outlines.html for the latest version.



SOT223					
Dim	Min	Max	Тур		
Α	1.55	1.65	1.60		
A1	0.010	0.15	0.05		
b	0.60	0.80	0.70		
b1	2.90	3.10	3.00		
С	0.20	0.30	0.25		
D	6.45	6.55	6.50		
E	3.45	3.55	3.50		
E1	6.90	7.10	7.00		
е	-	-	4.60		
e1	-	-	2.30		
L	0.85	1.05	0.95		
Q	0.84	0.94	0.89		
All [All Dimensions in mm				

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.



SOT223

SOT223

Dimensions	Value (in mm)
С	2.30
C1	6.40
Х	1.20
X1	3.30
Y	1.60
Y1	1.60
Y2	8.00



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